Mikhail V Yakunin

List of Publications by Year
in descending order

65	251	1162889 8	1199470 12
papers	citations	h-index	g-index

66	66	66	148
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	On the Thermal Activation of Conductivity Electrons in a p-Type HgTe/CdHgTe Double Quantum Well with HgTe Layers of Critical Width. Semiconductors, 2019, 53, 919-922.	0.2	3
2	Effect of exchange electron-electron interaction on conductivity of InGaAs single and double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2019, 113, 14-20.	1.3	1
3	HgTe quantum wells with inverted band structure: Quantum Hall effect and the large-scale impurity potential. Low Temperature Physics, 2019, 45, 412-418.	0.2	4
4	Scaling laws under quantum Hall effect for a smooth disorder potential. Low Temperature Physics, 2019, 45, 176-180.	0.2	1
5	On the issue of universality of critical exponents in the quantum Hall effect mode. Low Temperature Physics, 2019, 45, 181-188.	0.2	2
6	â€œExtremum Loopâ€•Model for the Valence-Band Spectrum of a HgTe/HgCdTe Quantum Well with an Inverted Band Structure in the Semimetallic Phase. Semiconductors, 2018, 52, 1403-1406.	0.2	3
7	Nonuniversal Scaling Behavior of Conductivity Peak Widths in the Quantum Hall Effect in InGaAs/InAlAs Structures. Semiconductors, 2018, 52, 1551-1558.	0.2	2
8	Electron Effective Mass and g Factor in Wide HgTe Quantum Wells. Semiconductors, 2018, 52, 12-18.	0.2	4
9	Quantum Hall effect in n-InGaAs/InAlAs metamorphic nanoheterostructures with high InAs content. Journal of Magnetism and Magnetic Materials, 2017, 440, 10-12.	1.0	3
10	The temperature dependence of the conductivity peak values in the single and the double quantum well nanostructures n-InGaAs/GaAs after IR-illumination. Semiconductors, 2017, 51, 272-278.	0.2	1
11	Conditions for experimental observation of the critical behavior of the longitudinal and Hall resistance in the quantum Hall regime in gallium and indium arsenide-based heterostructures. Low Temperature Physics, 2017, 43, 478-484.	0.2	0
12	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490.	0.2	3
13	Insulator-quantum Hall transition in n-InGaAs/GaAs heterostructures. Low Temperature Physics, 2017, 43, 491-494.	0.2	2
14	Antisymmetric contribution to the magnetoresistance of heterostructures in a parallel magnetic field. Low Temperature Physics, 2017, 43, 495-498.	0.2	0
15	HgTe/CdHgTe double quantum well with a spectrum of bilayer graphene and peculiarities of its magnetotransport. JETP Letters, 2016, 104, 403-410.	0.4	11
16	Magnetotransport in double quantum well with inverted energy spectrum: HgTe/CdHgTe. Physical Review B, 2016, 93, .	1.1	16
17	Quantum Hall effect and hopping conductivity in n-InGaAs/InAlAs nanoheterostructures. Semiconductors, 2016, 50, 1641-1646.	0.2	2
18	2Dâ€localization and delocalization effects in quantum Hall regime in HgTe wide quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 473-476.	0.8	4

#	Article	IF	Citations
19	Variable-Range Hopping Conductivity in Quantum Hall Regime for HgTe-Based Heterostructure. Journal of Low Temperature Physics, 2016, 185, 665-672.	0.6	6
20	Quantum magnetotransport inn-InGaAs/GaAs structures with electron density changes caused by infrared radiation. Low Temperature Physics, 2015, 41, 221-232.	0.2	4
21	Temperature scaling in the quantum-Hall-effect regime in a HgTe quantum well with an inverted energy spectrum. Semiconductors, 2015, 49, 1545-1549.	0.2	11
22	Electron-electron interaction and the universality of critical indices for quantum Hall effect plateau-plateau transitions in n-InGaAs/GaAs nanostructures with double quantum wells. Semiconductors, 2015, 49, 181-186.	0.2	1
23	Quantum Hall plateau-plateau transitions inn-InGaAs/GaAs heterostructures before and after IR illumination. Low Temperature Physics, 2015, 41, 106-111.	0.2	6
24	Scaling in the Quantum Hall Regime for a Double Quantum Well Nanostructure in High Magnetic Field. Solid State Phenomena, 2014, 215, 208-213.	0.3	0
25	Quantum Phase Transition in HTSC Thick Films: YBa2Cu3O x , YBa2Cu3O x (5 % Ag-Doped) in a Strong Pulsed Magnetic Field up to 32 T at Low Temperatures (58â€“100 K), Current Densities and Stress-Effect. Journal of Superconductivity and Novel Magnetism, 2013, 26, 639-649.	0.8	0
26	Scaling in the quantum Hall effect regime in n-InGaAs/GaAs nanostructures. Journal of Experimental and Theoretical Physics, 2013, 117, 144-152.	0.2	8
27	Temperature dependence of quantum lifetime inn-InGaAs/GaAs structures with strongly coupled double quantum wells. Low Temperature Physics, 2013, 39, 43-49.	0.2	5
28	Tunneling effects in tilted magnetic fields in n-InGaAs/GaAs structures with strongly coupled double quantum wells. Semiconductors, 2013, 47, 1447-1451.	0.2	1
29	The effect of infrared radiation on quantum magnetotransport in n-InGaAs/GaAs with two strongly coupled quantum wells. Low Temperature Physics, 2013, 39, 374-377.	0.2	6
30	Temperature dependence of the bandwidth of delocalized states for n-InGaAs/GaAs in the quantum Hall effect regime. Low Temperature Physics, 2013, 39, 50-57.	0.2	2
31	Effects of spin polarization in the HgTe quantum well. Physical Review B, 2012, 85, .	1.1	11
32	A problem of the effective g-factor in the n-HgTeâˆ•Cd[sub x]Hg[sub 1âˆ’x]Te quantum well with inverted band structure. , 2011, , .		0
33	Interlevel hybridization phenomena in the coincidence effect under quantum Hall regime in a HgTe quantum well. Journal of Physics: Conference Series, 2011, 334, 012030.	0.3	1
34	Spin Polarization Phenomena and Pseudospin Quantum Hall Ferromagnetism in the HgTe Quantum Well. AIP Conference Proceedings, 2011, , .	0.3	0
35	Spin splittings in the n- quantum well with inverted band structure. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 948-951.	1.3	19
36	Quantum Hall effect in an InAsâˆ•AlSb double quantum well. Low Temperature Physics, 2009, 35, 44-47.	0.2	1

#	Article	IF	Citations
37	Magnetotransport in two-dimensional n-InGaAsâˆ•GaAs double-quantum-well structures near the transition from the insulator to the quantum Hall effect regime. Low Temperature Physics, 2009, 35, 32-43.	0.2	14
38	Effect of impurity potential range on a scaling behavior in the quantum Hall regime. Physica B: Condensed Matter, 2009, 404, 5192-5195.	1.3	2
39	Spectrum of Landau levels of a double quantum well in an inclined magnetic field. Low Temperature Physics, 2009, 35, 133-136.	0.2	3
40	Evolution of the spin-split quantum Hall states with magnetic field tilt in the InAs-based double quantum wells. Journal of Physics: Conference Series, 2009, 150, 022100.	0.3	3
41	Investigation of Magneto-Resistance Behavior in High Pulsed Magnetic Fields up to 35ÂT of YBa2Cu3O x and YBa2Cu3O x (5%ÂAg-doped) Thick Films Near 77 K. Journal of Superconductivity and Novel Magnetism, 2008, 21, 161-162.	0.8	1
42	Tilted magnetic field quantum magnetotransport in the double quantum well with a sizable bulk g-factor: InxGa1âˆ’xAs/GaAs. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1451-1453.	1.3	3
43	Quantum Hall effect in p-Geâˆ•Ge1âˆ’xSix heterostructures with low hole mobility. Low Temperature Physics, 2007, 33, 147-150.	0.2	2
44	STEREOSCOPIC OSCILLATIONS OF THE n-InGaAs/GaAs DOUBLE QUANTUM WELL MAGNETORESISTANCE UNDER TILTED MAGNETIC FIELDS. International Journal of Modern Physics B, 2007, 21, 1399-1403.	1.0	0
45	TRANSPORT PROPERTIES OF 2D ELECTRON GAS IN AN n-InGaAs/GaAs DQW IN A VICINITY OF LOW MAGNETIC-FIELD-INDUCED HALL INSULATORâ€“QUANTUM HALL LIQUID TRANSITION. International Journal of Nanoscience, 2007, 06, 173-177.	0.4	0
46	Features of quantum effects in two-dimensional GaAsâˆ•nâ€InGaAsâˆ•GaAs structures with double quantum wells. Low Temperature Physics, 2007, 33, 156-159.	0.2	6
47	Quantum magnetotransport in an n-InxGa1âˆ’xAsâˆ•GaAs double quantum well in tilted magnetic fields. Low Temperature Physics, 2007, 33, 151-155.	0.2	1
48	Transport Properties of 2D-Electron Gas in a InGaAs/GaAs DQW in a Vicinity of Low Magnetic-Field-Induced Insulator-Quantum Hall Liquid Transition. AIP Conference Proceedings, 2007, , .	0.3	2
49	Magnetic breakdown and quantum magnetotransport with a constant pseudospin under tilted magnetic fields in an n-In x Ga1âˆ’x As/GaAs double quantum well. Journal of Experimental and Theoretical Physics, 2007, 105, 214-222.	0.2	5
50	Effect of spin-orbit coupling on the spectrum of two-dimensional electrons in a magnetic field. Semiconductors, 2007, 41, 1092-1100.	0.2	9
51	Transport properties of two-dimensional hole gas in a Ge1âˆ’x Si x /Ge/Ge1âˆ’x Si x quantum well in the vicinity of metal-insulator transition. Semiconductors, 2007, 41, 1315-1322.	0.2	1
52	Spin effects in magnetoresistance induced in an n-InxGa1âˆ’x As/GaAs double quantum well by a parallel magnetic field. Semiconductors, 2005, 39, 107-112.	0.2	10
53	Galvanomagnetic study of the quantum-well valence band of germanium in the Ge1âˆ’xSix/Ge/Ge1âˆ’xSix potential well. Physics of the Solid State, 2005, 47, 49-53.	0.2	1
54	MULTI-VALENCE-SUBBAND MAGNETOTRANSPORT IN A MODULATION-DOPED p-TYPE Ge1-xSix/Ge/Ge1-xSix QUANTUM WELL. International Journal of Modern Physics B, 2004, 18, 3641-3644.	1.0	0

#	Article	IF	Citations
55	Parallel magnetic field-induced magnetoresistance peculiarities of the double quantum well filled with electrons or holes. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 68-71.	1.3	2
56	Formation of a self-consistent double quantum well in a wide p-type quantum well. Low Temperature Physics, 2004, 30, 871-873.	0.2	0
57	Magnetotransport probing of the quality of the heterointerfaces and degree of symmetry of the potential profile of quantum wells in the valence band of the Ge1â^'xSix/Ge/Ge1â^'xSix heterosystem. Low Temperature Physics, 2004, 30, 853-857.	0.2	0
58	Nonmonotonic temperature dependence of the resistivity of p-Ge/Ge1â^'xSix in the region of the metalâ€“insulator transition. Low Temperature Physics, 2004, 30, 867-870.	0.2	7
59	Reconstruction of the 2D hole gas spectrum for selectively doped p-Ge/Ge1â^'x Six heterostructures. Journal of Experimental and Theoretical Physics, 2003, 96, 118-128.	0.2	4
60	<title>Parallel magnetic field induced strong negative magnetoresistance in a wide p-Ge<formula><inf><roman>1-x</roman></inf></formula>Si<formula><inf><roman>x</roman></inf></formula>/Ge/p-Ge<formula><inf>quantum well</title>. , 2002, 5023, 190.	0	
61	The key role of a smooth impurity potential in formation of the hole spectrum for p-Ge/Ge1-xSixheterostructures in the quantum Hall regime. Nanotechnology, 2002, 13, 86-93.	1.3	13
62	Evaluation of mobility gaps and density of localized hole states in p-Ge/Ge1â^'x Six heterostructures in the quantum Hall effect mode. Semiconductors, 2002, 36, 519-526.	0.2	5
63	Probing the p-Ge1-xSix/Ge/p-Ge1-xSixquantum well by means of the quantum Hall effect. Nanotechnology, 2000, 11, 351-358.	1.3	8
64	Bistability of quantum magnetotransport in a multilayer Ge/p-Ge1â^'x Six heterostructure with wide potential wells. JETP Letters, 1999, 70, 301-308.	0.4	3
65	The quantum Hall effect in a wide p-Ge1â^'x Six/Ge/p-Ge1â^'x Six potential well. Semiconductors, 1998, 32, 649-656.	0.2	2